Advance Information NCS35011

The NCS35011 is an ultra-low power protection integrated circuit managing lithium-ion batteries from 3 to 5 cells in series with accurate battery voltage indication up to 5 LED outputs.

Each cell in the battery pack is monitored for an over-voltage and under-voltage condition. Upon detecting an over-voltage, the ODI pin will assert indicating a fault condition and stay asserted until the fault is cleared. During an under voltage condition, the UDI pin will also assert indicating the fault but will have a pulse width that is pre-set in the protector. Both over and under voltage detections have a hard coded pre-set delay time before fault indication.

Pulling the ENB high will start a measurement of the battery pack voltage which will be compared to a pre-set detection threshold table. If a threshold voltage is exceeded the protector will power the corresponding LED to indicate state of charge of the pack.

Hardware protection and battery monitoring run autonomously and allows operation without a microcontroller.

Features

- Over-Voltage (OV) and Under-Voltage (UV) Detection
- Protection for 3, 4 and 5 Series Cells
- State of Charge (SoC) Indication with High Voltage Tolerant LED Drivers
- Configurable Fault Outputs (Active High or Low for Push–Pull or Open Drain)
- High-Accuracy Voltage Measurement ±5 mV
- Low Power Consumption $I_{cc} = 4 \mu A$
- Input BAT Voltage Range 5 V to 28 V, tolerant to 70 V for Increased Immunity to Surge
- Extended Junction Temperature Range to 125°C
- These Devices are Pb-Free and are RoHS Compliant

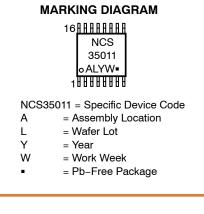
Applications

- Secondary Protection
- Power and Gardening Tools
- Portable/Autonomous Equipment (Cleaners, Mowers, Motive, Medical)

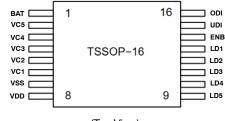
This document contains information on a new product. Specifications and information herein are subject to change without notice.



TSSOP-16 CASE 948F







(Top View)

ORDERING INFORMATION

| Device | Package | Shipping [†] |
|----------------|-----------------------|-----------------------|
| NCS35011DTBR2G | TSSOP-16 (Pb-Free) | 2500 / Tape & Reel |

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

Block Diagram

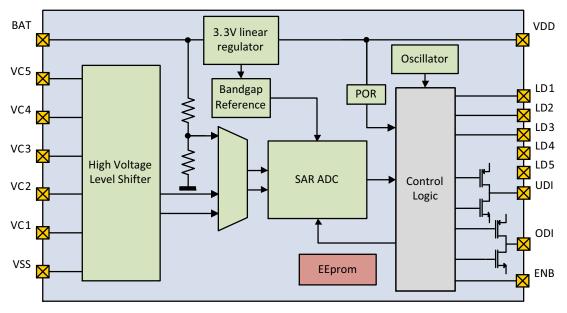
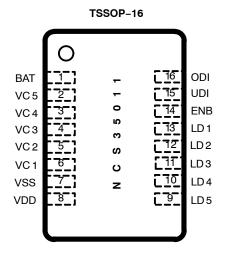


Figure 1. Simplified Block Diagram

Pin Connections





PIN DESCRIPTION

| Signal Name | Pin No. | Туре | Description |
|-------------|---------|-------------------|--------------------------------------|
| BAT | 1 | Power | Positive Battery input voltage |
| VC5 | 2 | Analog | Battery cell 5 voltage |
| VC4 | 3 | Analog | Battery cell 4 voltage |
| VC3 | 4 | Analog | Battery cell 3 voltage |
| VC2 | 5 | Analog | Battery cell 2 voltage |
| VC1 | 6 | Analog | Battery cell 1 voltage |
| VSS | 7 | Ground | Negative Battery input voltage |
| VDD | 8 | Power | 3.3 V regulator output voltage |
| LD5 | 9 | Output Open Drain | LED output 5, open drain; active low |

PIN DESCRIPTION (continued)

| Signal Name | Pin No. | Туре | Description |
|-------------|---------|-------------------|--|
| LD4 | 10 | Output Open Drain | LED output 4, open drain; active low |
| LD3 | 11 | Output Open Drain | LED output 3, open drain; active low |
| LD2 | 12 | Output Open Drain | LED output 2, open drain; active low |
| LD1 | 13 | Output Open Drain | LED output 1, open drain; active low |
| ENB | 14 | Input | LED output indication enable input; pull down, active high |
| UDI | 15 | Output | Cell Under voltage detection output indication; configurable (CMOS active low or high; nFET open drain active on or off) |
| ODI | 16 | Output | Cell over voltage detection output indication; configurable (CMOS active low or high; nFET open drain active on or off) |

ABSOLUTE MAXIMUM RATINGS

| Rating | Symbol | Value | Unit |
|--|---------------------|------------------|------|
| Input voltage (Note 1) | V _{BAT} | –0.5 to 70 | V |
| Supply Current | I _{BAT} | 10 | mA |
| VC1, VC2, VC3, VC4, VC5, ODI, UDI, LD1, LD2, LD3, LD4, LD5 voltage | V _{IHV} | –0.5 to 70 | V |
| ENB, NC voltage | V _{ILV} | V _{BAT} | V |
| VCn – VCn–1 differential cell input voltages | V _{CELLD} | –0.5 to 30 | V |
| Maximum Junction Temperature | T _{J(max)} | 125 | °C |
| Storage Temperature Range | T _{STG} | –55 to 150 | °C |
| ESD Capability, Human Body Model (Note 2) | ESD _{HBM} | 2 | kV |
| ESD Capability, Charge Device Model (Note 2) | ESD _{CDM} | 500 | V |
| Lead Temperature Soldering Reflow (SMD Styles Only), Pb–Free Versions (Note 3) | T _{SLD} | 260 | °C |

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected. 1. Refer to ELECTRICAL CHARACTERISTICS, RECOMMENDED OPERATING RANGES and/or APPLICATION INFORMATION for Safe

Operating parameters.

2. This device series incorporates ESD protection and is tested by the following methods: ESD Human Body Model tested per AEC-Q100-002 (EIA/JESD22-A114) ESD Machine Model tested per AEC-Q100-003 (EIA/JESD22-A115)

Latchup Current Maximum Rating: ≤100 mA per JEDEC standard: JESD78

3. For information, please refer to our Soldering and Mounting Techniques Reference Manual, SOLDERRM/D

THERMAL CHARACTERISTICS

| Rating | Symbol | Value | Unit |
|--|--------------------------------------|-------|------|
| Thermal Characteristics, TSSOP-16 (Note 1) Thermal Resistance, Junction-to-Air (Note 5) Thermal Reference, Junction-to-Case (Note 5) | R _{θJA} R _{ψJC} | 115 | °C/W |

4. Values based on copper area of 645 mm² (or 1 in²) of 1 oz copper thickness and FR4 PCB substrate.

RECOMMENDED OPERATING RANGES

| Rating | Symbol | Min | Тур | Max | Unit |
|--|-------------------|-----|-----|------------------|------|
| BAT Input voltage | V _{BAT} | 5 | 18 | 28 | V |
| Cell voltage (VC1, VC2, VC3, VC4, VC5) | V _{CELL} | 2 | | 5 | V |
| ODI, UDI voltage | V _{PRES} | 0 | | V _{BAT} | V |
| LED voltage (LD1, LD2, LD3, LD4, LD5) | V _{LED} | 0 | | V _{BAT} | V |
| ENB voltage | V _{EN} | 0 | | V _{BAT} | V |
| Ambient Temperature | T _A | -40 | | 85 | °C |

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

DC ELECTRICAL SPECIFICATIONS

ENB Debounce for SoC Indication (Note 5)

| Rating | Symbol | Min | Тур | Max | Unit |
|--|----------------------|-------|------------------------|-----|------|
| VOLTAGE MONITORING (VC1, VC2, VC3, VC4, VC5 and BAT) | | | | | |
| BAT Voltage Detection Accuracy ($T_A = 25^{\circ}C$) | V _{BAT_QA} | | <75 | | mV |
| Cell Voltage Detection Accuracy ($T_A = 25^{\circ}C$, VCx = 3V to 4.7V) | V _{OA} | -5 | | 5 | mV |
| Cell Voltage Detection Accuracy Across Temperature ($T_A = -40$ to $85^{\circ}C$) | V _{OAD} | -30 | | 30 | mV |
| Overvoltage Detection (OVD) Range (Note 5) | V _{OVD} | 3.6 | | 4.7 | V |
| Overvoltage Detection Hysteresis (OVH) Range (Note 5) | V _{OVH} | 50 | | 500 | mV |
| Undervoltage Detection (UVD) Range (Note 5) | V _{UVD} | 1.5 | | 2.8 | V |
| Undervoltage Detection Hysteresis (UVH) Range (Note 5) | V _{UVH} | 50 | | 500 | mV |
| BAT Voltage to Active LD1 Pin for SoC Indication | V _{DET1} | | Table 2 | | V |
| BAT Voltage to Active LD1-2 Pin for SoC Indication | V _{DET2} | | Table 2 | | V |
| BAT Voltage to Active LD1–3 Pin for SoC Indication | V _{DET3} | | Table 2 | | V |
| BAT Voltage to Active LD1-4 Pin for SoC Indication | V _{DET4} | | Table 2 | | V |
| BAT Voltage to Active LD1–5 Pin for SoC Indication | V _{DET5} | | Table 2 | | V |
| SUPPLY AND LEAKAGE CURRENT | | | | | - |
| Supply Current – Standby mode with no fault and ENB low | I _{CC} | | 4 | | μA |
| Input Current at VCx pins | I _{IN} | -0.1 | | 0.1 | μA |
| Supply Current – State of Charge Mode (ENB=3.6V,LDx=0,VCx=4V, T _A = 25°C) | I _{SOC} | | 26 | | μA |
| ODI/UDI OUTPUT PIN, CMOS ACTIVE HIGH OR LOW VERSION | | | | | - |
| ODI/UDI Active High Across Temperature ($I_{ODI-H} \le 5$ mA, *Tested with $V_{BAT}=5V$) | V _{ODI-H} | | *V _{BAT} -1.7 | | V |
| ODI/UDI Active Low Across Temperature ($I_{ODI-L} \leq 5 \text{ mA}$) | V _{ODI-L} | | 0.1 | | V |
| OUTPUT DRIVE ODI/UDI, OPEN DRAIN NMOS FET ACTIVE ON OR OFF VER | | | | | - |
| Static Drain–Source On–Resistance (nFET On–Resist), I _{ODI} = 5mA, T _A = 110°C | R _{DS-ON} | | | 15 | Ω |
| ODI/UDI Off Current | I _{ODI-OFF} | | | 0.1 | μA |
| ENB INPUT | | | | | - |
| ENB Input Voltage "High" | V _{EN-H} | | 1.5 | | V |
| ENB Input Voltage "Low" | V _{EN-L} | | 1.3 | | V |
| ENB Pull Down Current | I _{PD} | | 50 | | kΩ |
| LED OUTPUT CURRENT DRIVE | | | | | - |
| Output Sink Current | I _{LED-ON} | | | 10 | mA |
| Output Leakage Current | I _{LED-OFF} | | | 0.1 | μA |
| TIMING REQUIREMENTS | | | | | - |
| Rating | Symbol | Min | Тур | Max | Unit |
| DELAY TIMER | | | | | |
| Overvoltage Delay Time (ODEL) Configuration Range (Note 5) | todel | 0.94 | Table 3 | 5 | s |
| Undervoltage Delay Time (UDEL) Configuration Range (Note 5) | t _{UDEL} | 0.125 | Table 3 | 1 | s |
| Undervoltage Pulse Time (UPUL) Configuration Range (Note 5) | t _{UPUL} | 1 | Table 3 | 5 | s |
| Delay/pulse Response Timing Accuracy (T _A = 25°C) | t _{error} | -6% | | 6% | 1 |
| | -1 | 1 | 1 | | 1 |
| Delay/pulse Response Timing Accuracy Across Temperature ($T_A = -40$ to $85^{\circ}C$) | t _{error} | | 6% | | |

LDx Pulse Duration (LEDD) Time Configuration Range (Note 5)tt0.05Table 35s5. These configurations are programmed at the factory, they are not customer programmable. However, for high volumes, **onsemi** can define

30

t_{ENB}

55

ms

 These configurations are programmed at the factory, they are not customer programmable. However, for high volumes, onsemi can define further IC variants with any combination of the shown configurations NCS35011DBxyR2G. Contact your sales representative.

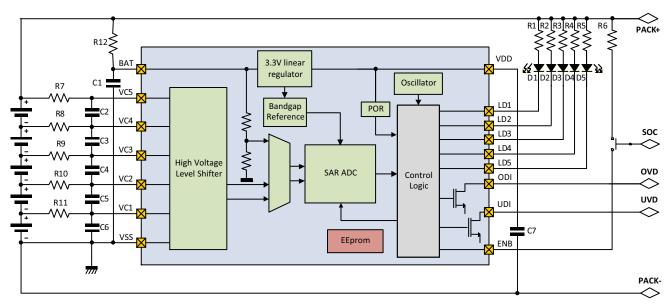


Figure 3. 5S Battery Pack, 5 LEDs, Open Drain Outputs Application Diagram

| Component Type | Instance | Value | Note |
|----------------|------------------|--------|---|
| LED | D1,D2,D3,D4,D5 | - | LEDs for state of charge indication |
| Capacitor | C1 | 1 μF | Battery pack voltage capacitor |
| Capacitor | C2,C3,C4,C5,C6 | 100 nF | Input cell voltage filter capacitor |
| Capacitor | C7 | 1 μF | 3.3V regulator output filter capacitor |
| Resistor | R1,R2,R3,R4,R5 | 4.7 kΩ | LED current limiting resistor, set according to desired brightness; To guarantee the chip spec, it is recommended to limit each LED current less 10 mA. |
| Resistor | R6 | 1 kΩ | Limiting resistor for switch input refer to ENB pull-down current spec to set the resistance |
| Resistor | R7,R8,R9,R10,R11 | 1 kΩ | Input cell voltage filter resistor |
| Resistor | R12 | 1 kΩ | Battery input filter resistor; Limit R12 resistance when IC ODI/UDI pin is configured as CMOS push/pull (Note 6) |

6. All VC pin internal high side ESD diodes are connected to BAT pin for ESD protection purpose. When ODI/UDI pin is driving a resistive load and consume a large current through BAT pin, a large IR drop through R12 may result VC5 pin voltage higher than BAT pin and forward bias VC5 pin internal high side ESD diode.

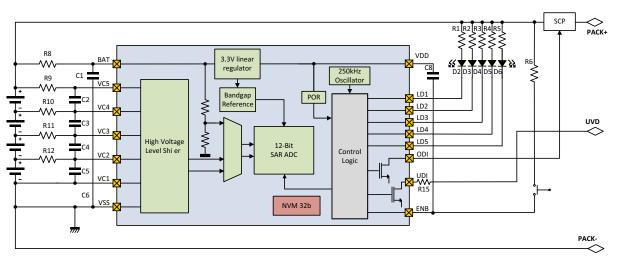


Figure 4. 4S Battery Pack, 5 LEDs, Open Drain Outputs with SCP Application Diagram

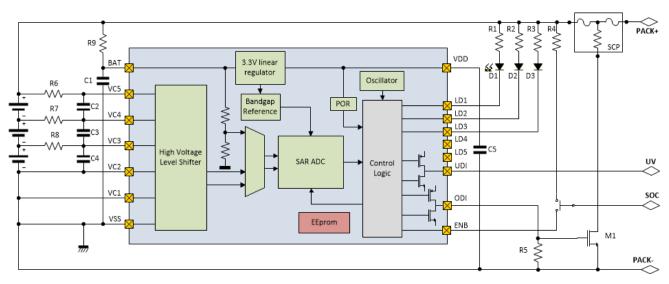


Figure 5. 3S Battery Pack, 3 LEDs, Push–Pull Outputs with SCP Application Diagram Note: Having series resistor on VC2 and VC1 will help with system level ESD

Detailed Description

The NCS35011 is an individual cell-monitoring device that checks for over and under voltage conditions in 3 to 5S battery packs. Figure 3–5 shows the 3, 4, and 5 series of battery pack application diagram, and the IC expect VC1/VC2 to be grounded in 3S and VC1 to be grounded in 4S application. The device also monitors the pack voltage and drives LEDs that indicate the voltage level for a rudimentary state of charge indication.

Overvoltage and Under-voltage Detection

Monitoring for an overvoltage condition occurs by comparing each cell voltage (VCx) with a predetermined threshold set by the parameter VOV. An on-chip ADC samples each cell voltages every 125 ms, so this can affect the overvoltage and under-voltage response time. If any cell voltage goes above the V_{OV} threshold for the predetermined t_{DEL-OV} time limit, the IC will actuate the ODI pin depending on the pin configuration to indicate a fault. If all of the individual cell voltages drop back down below the V_{OV} threshold, the ODI pin will default back to the normal operational state. ODI pin will either pull low internally (recommend to limit this current less than 5 mA), if configured as nFET active low, or will be pulled high through external pull-up resistor, if configured as nFET active high impedance; ODI pin can also be configured as CMOS active low or high.

Under-voltage detection occurs by comparing each cell voltage (VCx) with a predetermined threshold set by the parameter V_{UV} . If any cell voltage goes below the V_{UV} threshold for the t_{DEL-UV} time limit, the IC will assert the UDI pin to indicate a fault. A fault indication will assert the UDI pin for the time duration specified by the parameter t_{ON-UV} . A cell voltage recovery back to a normal level will

not interrupt the UDI signaling. To detect a new under-voltage fault condition all cell voltages will need to return to a normal level and then drop below the V_{UV} threshold for the specified delay time t_{DEL-UV} . UDI pin will either pull low internally (recommend to limit this current less than 5mA), if configured as nFET active low, or will be pulled high through external pull-up resistor, if configured as nFET active high impedance; UDI pin can also be configured as CMOS active low or high.

Figure 6 shows timing waveforms of the overvoltage and under-voltage fault detection. Table 1 lists key parameters for each of the fault conditions.

Battery Pack Voltage State of Charge Indication

When the ENB pin asserts high for the time limit set by t_{ENB} the NCS37011 will measure the voltage at the BAT pin and compare it to the thresholds set by V_{DETX} . If the detection level exceeds the predetermined threshold, the appropriate LDx open drain pulldown will assert turning on the corresponding LED for the time duration $t_{PUL-LED}$ and then shut off. To restart the LEDs the ENB pin will assert low for the time limit t_{ENB} and then assert high again for the same amount of time. Figure 6 shows the ENB input timing waveform for state of charge indication.

NCS37011 has 4 multiplier sets to choose from, shown in Table 2. The threshold voltage for different LED pin to turn on are dependent upon number of cells (VC_COUNT) in the battery pack and the configured over voltage (OVD) per cell. Each LED threshold is set by multiplying a constant (Multiplier) times the product of VC_COUNT and OVD. This creates the typical threshold V_{DETX}.

Product = VC_COUNT * OVD;

V_{DETX} = Product * Multiplier.

| Tab | le | 2. |
|-----|----|----|
|-----|----|----|

| SoC Multiplier Sets | LED pin (LDx) | Symbol (V _{DETX}) | Multiplier |
|---------------------|---------------|-----------------------------|------------|
| А | LD5 | V _{DET5} | 0.954 |
| | LD4 | V _{DET4} | 0.936 |
| | LD3 | V _{DET3} | 0.898 |
| | LD2 | V _{DET2} | 0.837 |
| | LD1 | V _{DET1} | 0.585 |
| В | LD5 | V _{DET5} | 0.918 |
| | LD4 | V _{DET4} | 0.875 |
| | LD3 | V _{DET3} | 0.847 |
| | LD2 | V _{DET2} | 0.819 |
| | LD1 | V _{DET1} | 0.781 |
| С | LD5 | V _{DET5} | 0.877 |
| | LD4 | V _{DET4} | 0.847 |
| | LD3 | V _{DET3} | 0.788 |
| | LD2 | V _{DET2} | 0.765 |
| | LD1 | V _{DET1} | 0.729 |

Table 2.

| SoC Multiplier Sets | LED pin (LDx) | Symbol (V _{DETX}) | Multiplier |
|---------------------|---------------|-----------------------------|------------|
| D | LD5 | V _{DET5} | 0.931 |
| | LD4 | V _{DET4} | 0.883 |
| | LD3 | V _{DET3} | 0.841 |
| | LD2 | V _{DET2} | 0.756 |
| | LD1 | V _{DET1} | 0.659 |

NOTE: Depends on the application, user may combine or skip certain LED pins to create a desired SoC combination. Unused LED pin can be floated.

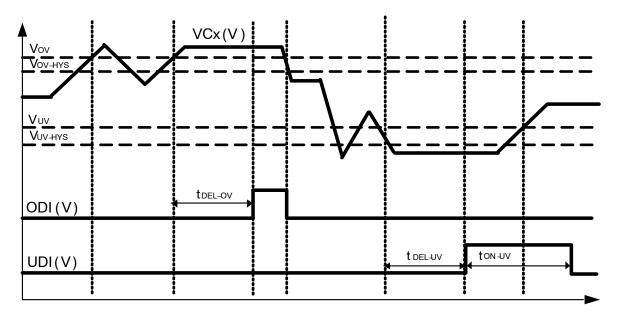


Figure 6. Timing for OV and UV Detection

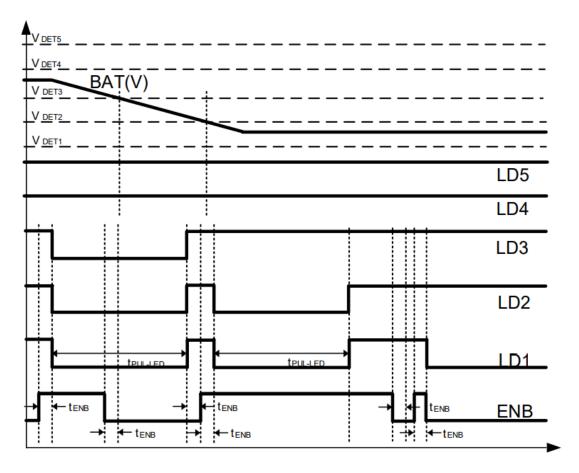


Figure 7. ENB Input Timing for State of Charge Indication

Table 3. ORDERABLE PART DIFFERENTIATION

| Part Number | 3/4/5 S | OVD (V) | OVH (V) | UVD (V) | UVH (V) | ODEL (s) | UDEL (s) | UPUL (s) | OV Output | OV Polarity | UV Output | UV Polarity | LEDD (s) | SoC sets |
|-----------------------|---------|-------------|--------------|-------------|--------------|---------------|-------------|-------------|--------------|----------------|--------------|----------------|-------------|-------------|
| NCS35011D- TBR2G | 5 | 4.275 | 0.05 | 2 | 0.25 | 0.94 | 1 | 1.5 | OD | 1 | OD | 0 | 3 | А |
| NCS35011D- TBxyR2G | 3–5 | 3.6- 4.7 | 0.05 -0.5 | 1.5- 2.8 | 0.05 -0.5 | 0.94- 4.94 | 0.125 -1 | 1–5 | OD/PP | 0/1 | OD/PP | 0/1 | 0/3/5 | A/B/C/D |

NOTE: **OD** = nFET open drain; **PP** = CMOS push or pull;

nFET open drain (OV/UV polarity 0): active low (nFET ON);

nFET open drain (OV/UV polarity 1): active high impedance (nFET OFF);

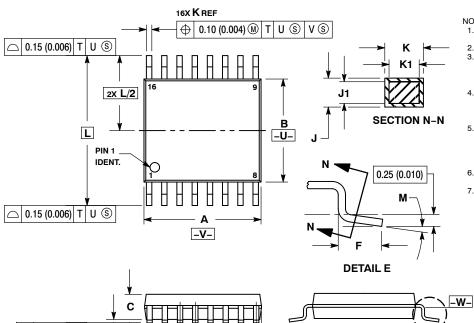
CMOS push-pull (OV/UV polarity 0): active low;

CMOS push-pull (OV/UV polarity 1): active high;

For high volumes, **onsemi** can define further IC variants with any combination of the shown configurations NCS35011DTBxyR2G. Contact your sales representative.

PACKAGE DIMENSIONS





G

○ 0.10 (0.004)

D

-T- SEATING PLANE

NOTES:

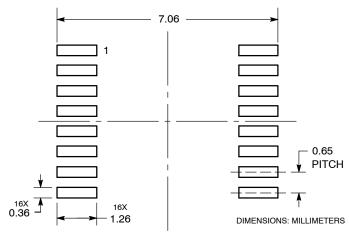
- NOTES:
 DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 CONTROLLING DIMENSION: MILLIMETER.
 DIMENSION A DOES NOT INCLUDE MOLD FLASH. PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED A 15 (0000) DED SUPE
- MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
 DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE.
 DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION. SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION.
 TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.
- REFERENCE ONLY. DIMENSION A AND B ARE TO BE
- 7. DETERMINED AT DATUM PLANE -W-.

| | MILLIN | IETERS | INCHES | | | |
|-----|--------|--------|-----------|-------|--|--|
| DIM | MIN | MAX | MIN | MAX | | |
| Α | 4.90 | 5.10 | 0.193 | 0.200 | | |
| В | 4.30 | 4.50 | 0.169 | 0.177 | | |
| С | | 1.20 | | 0.047 | | |
| D | 0.05 | 0.15 | 0.002 | 0.006 | | |
| F | 0.50 | 0.75 | 0.020 | 0.030 | | |
| G | 0.65 | BSC | 0.026 BSC | | | |
| Н | 0.18 | 0.28 | 0.007 | 0.011 | | |
| J | 0.09 | 0.20 | 0.004 | 0.008 | | |
| J1 | 0.09 | 0.16 | 0.004 | 0.006 | | |
| Κ | 0.19 | 0.30 | 0.007 | 0.012 | | |
| K1 | 0.19 | 0.25 | 0.007 | 0.010 | | |
| L | 6.40 | | 0.252 BSC | | | |
| Μ | 0 ° | 8 ° | 0 ° | 8 ° | | |

SOLDERING FOOTPRINT

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DETAIL E



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